#### SILICON (Si) POWER MOSFET A CEM3254



CET MOS

# **CEM3254**

## 30V ▲ 20mΩ ▲ 7.8A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type N-channel enhancement mode UL94V-0 rated flame retardant epoxy SO8 package ▲ MSL 3 Super high dense cell density for extremely low R<sub>DS(ON)</sub> High power and current handling capability





RoHS

REACH

#### **MAXIMUM RATINGS**

Parameter ( $T_A = 25^{\circ}C$ , unless otherwise noted)	Characteristics	
Drain-Source Voltage	V <sub>DS</sub>	30V
Gate-Source Voltage	V <sub>GS</sub>	±20V
Continuous Drain Current	Ι <sub>D</sub>	7.8A
Pulsed Drain Current Note 1	I <sub>DM</sub>	31.2A
Maximum Power Dissipation	PD	2.5W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +150°C

#### **THERMAL CHARACTERISTICS**

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Ambient Note 2	R <sub>th_ja</sub>	50°C/W

#### **APPLICATIONS**

Battery	DC	Load	Power	USB
Pack	Fan	Switches	Banks	Storage
+ 4 -			4	Ŷ

#### **PIN DESCRIPTION**

Circuit Diagram	Outline • Top View	Pin No.	Description
D (5,6,7,8)	8765 <b>889</b>	1	Source
		2 3	Source Source
G (4)		4 5	Gate Drain
<u>(                                    </u>		6 7	Drain Drain
l S (1,2,3)		8	Drain

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# **ELECTRICAL CHARACTERISTICS A** T<sub>A</sub> = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	30			V
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μA
Gate Body Leakage Current, Forward	$V_{GS} = 20V$ , $V_{DS} = 0V$	I <sub>GSSF</sub>			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	I <sub>GSSR</sub>			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250 \mu A$	V <sub>GS(th)</sub>	1		3	V
Static Drain-Source On-Resistance	$V_{GS} = 10V$ , $I_D = 4A$	R <sub>DS(ON)</sub>		20	28	mΩ
Static Drain-Source On-Resistance	$V_{GS}$ = 4.5V, I <sub>D</sub> = 3A	R <sub>DS(ON)</sub>		30	40	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS}$ = 15V, $V_{GS}$ = 0V, f = 1MHz	C <sub>ISS</sub>		360		рF
Output Capacitance	$V_{DS}$ = 15V, $V_{GS}$ = 0V, f = 1MHz	Coss		95		рF
Reverse Transfer Capacitance	$V_{DS}$ = 15V, $V_{GS}$ = 0V, f = 1MHz	C <sub>RSS</sub>		70		pF
Switching Characteristics Note 4						
Turn-On Delay Time	$V_{\text{DD}}$ = 15V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 7.8A, $R_{\text{G}(\text{ext})}$ = 2.7 $\Omega$	t <sub>D(ON)</sub>		12		ns
Turn-On Rise Time	$V_{\text{DD}}$ = 15V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 7.8A, $R_{\text{G}(\text{ext})}$ = 2.7 $\Omega$	t <sub>R</sub>		9		ns
Turn-Off Delay Time	$V_{DD}$ = 15V, $V_{GS}$ = 10V, $I_D$ = 7.8A, $R_{G(ext)}$ = 2.7 $\Omega$	t <sub>D(OFF)</sub>		26		ns
Turn-Off Fall Time	$V_{\text{DD}}$ = 15V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 7.8A, $R_{G(ext)}$ = 2.7 $\Omega$	t <sub>F</sub>		6		ns
Total Gate Charge	$V_{DS}$ = 15V, $V_{GS}$ = 10V, $I_D$ = 7.8A	Q <sub>G</sub>		10		nC
Gate Source Charge	$V_{DS}$ = 15V, $V_{GS}$ = 10V, $I_D$ = 7.8A	Q <sub>GS</sub>		0.7		nC
Gate Drain Charge	$V_{DS}$ = 15V, $V_{GS}$ = 10V, $I_{D}$ = 7.8A	$Q_{GD}$		3		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current <sup>Note 2</sup>		I <sub>S</sub>			2	А
Drain-Source Diode Forward Voltage <sup>Note 3</sup>	$V_{GS} = 0V$ , $I_S = 2A$	$V_{\text{SD}}$			1.2	V

#### Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

2: Surface Mounted on FR4 Board,  $t \le 10$  sec

3: Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

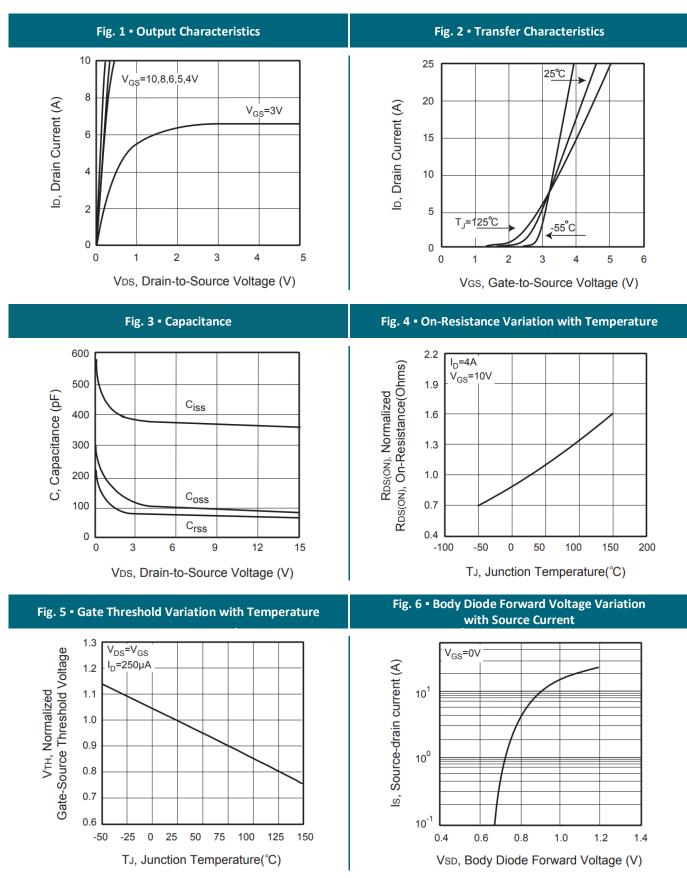
4: Guaranteed by design, not subject to production testing.



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### **REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE**



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#### **REFERENCE DATA A TYPICAL DEVICE PERFORMANCE**

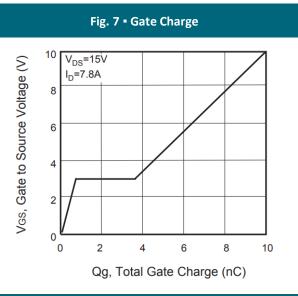
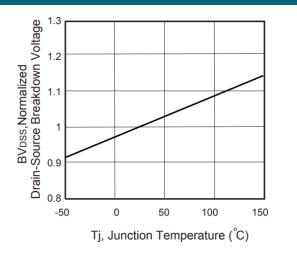


Fig. 9 - Breakdown Voltage Variation vs. Temperature



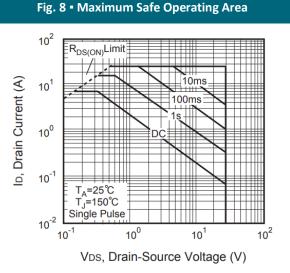
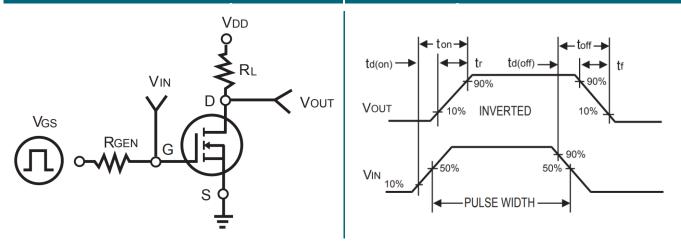


Fig. 10 • Switching Test Circuit





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## **REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE**

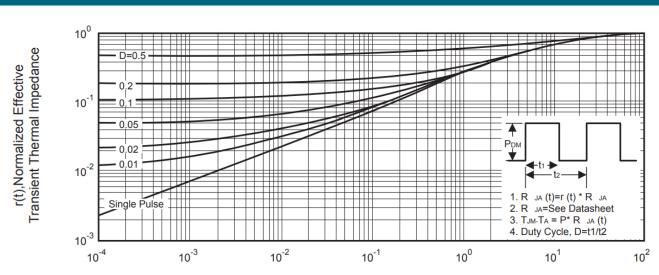
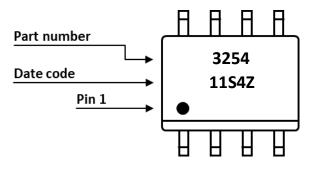


Fig. 12 • Normalized Thermal Transient Impedance Curve

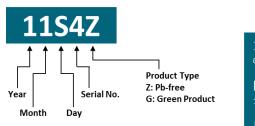
Square Wave Pulse Duration (sec)

#### **PART MARKING**



#### DATE CODE

Example: 11S4Z



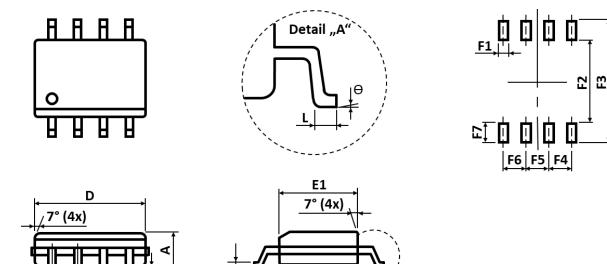
Coding list for "Day"										
1	2	3	4	5	6	7	8	9	Α	
01	02	03	04	05	06	07	08	09	10	
В	С	D	Ε	F	G	Н		J	K	
11	12	13	14	15	16	17	18	19	20	
L	Μ	Ν	0	Ρ	Q	R	S	Т	U	
21	22	23	24	25	26	27	28	29	30	
V										
31										

Coding list for "Month"





### PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters Millimeters (Min.) (Typ.)		Millimeters (Max.)
А	1.350	-	1.750	E1	3.700		4.060
A1	0.100	-	0.250	eB	5.800		6.200
В	0.310	-	0.510	е		1.270	
С	0.170	-	0.250	L	0.400		0.950
D	4.690	-	5.000	θ	0°	-	8°
Svm	Millimeters	Millimeters	Millimeters	Svm	Millimeters	Millimeters	Millimeters

eВ

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	0.500	-	F5	-	1.270	-
F2	-	4.250	-	F6	-	1.270	-
F3	-	6.250	-	F7	-	1.000	-
F4	_	1.270	-				

Notes: 1. The suggested land pattern dimensions have been provided for reference only. 2. For further information, please reference document IPC-7351A.

C

#### **ORDERING INFORMATION**

В

A1

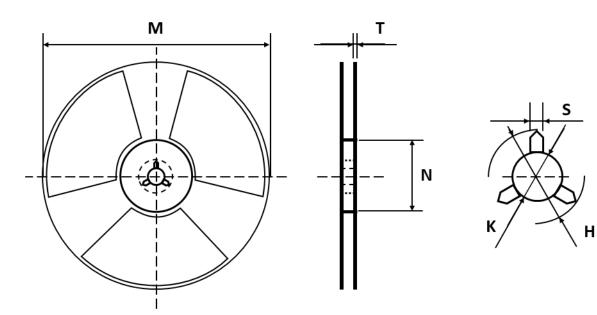
Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.	
CEM3254	SO8	13" Reel	2,500pcs	5,000pcs	40,000pcs	

Detail "A"



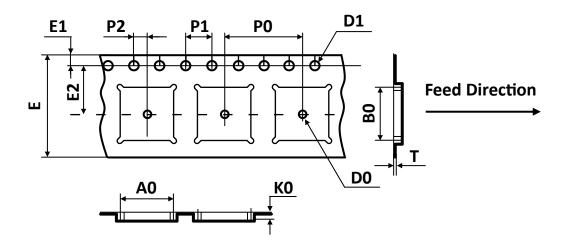


#### **REEL DIMENSIONS** All dimensions in mm



Tape Size	Reel Size	М	Ν	Т	Н	К	S
12mm	<i>d</i> 220	Ø330.00	Ø100.00	2.20	20.00	13.20	3.00
1211111	Ø330	±2.00	±0.50	±0.20	±1.00	±0.20	±1.00

#### **TAPE DIMENSIONS** All dimensions in mm



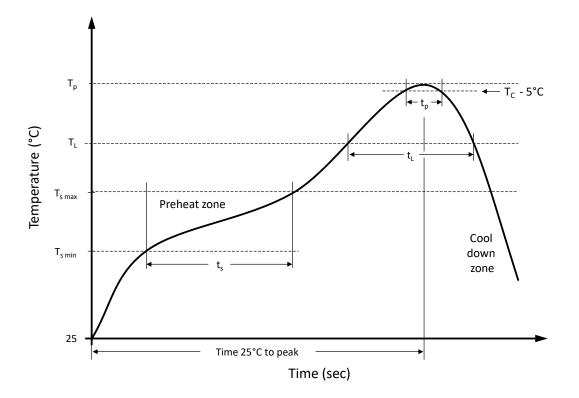
Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	т
SO8	6.50	5.30	2.05	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
308	±0.10	±0.10	±0.15	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.





#### **RECOMMENDED REFLOW SOLDERING PROFILE**



#### **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{smin}$	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time $t_s$ from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T <sub>L</sub> to T <sub>p</sub> )		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	TL	183 °C	217 °C
Time $t_L$ maintained above $T_L$	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t <sub>p</sub>	20 seconds max.	30 seconds max.
Ramp-down rate ( $T_L$ to $T_p$ )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



## **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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